



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

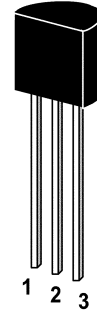
TEL: 852-2790 0314 FAX: 852-2790 0206

ST 2SA928

PNP Silicon Epitaxial Planar Transistor
for audio power amplifier

The transistor is subdivided into two groups, O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

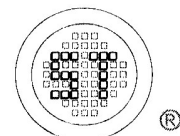


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.18g

Absolute Maximum Ratings (Ta=25°C)

	Symbol	Value	Unit
Collector to Base Voltage	$-V_{CBO}$	30	V
Collector to Emitter Voltage	$-V_{CEO}$	30	V
Emitter to Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	2	A
Power Dissipation	P_{tot}	1	W
Operating and Storage Junction Temperature	T_j, T_s	-55 to +150	°C



SEMTECH

Dated : 07/12/2002



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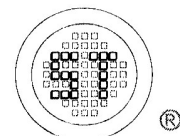
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Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE}=2V, -I_C=500mA$	O	h_{FE}	100	-	200	-
	Y	h_{FE}	160	-	320	-
Collector Cutoff Current at $-V_{CB}=30V$	$-I_{CBO}$	-	-	0.1	μA	
Emitter Cutoff Current at $-V_{EB}=5V$	$-I_{EBO}$	-	-	0.1	μA	
Collector-Emitter Breakdown Voltage at $-I_C=10mA$	$-V_{(BR)CEO}$	30	-	-	V	
Collector-Base Breakdown Voltage at $-I_C=100\mu A$	$-V_{(BR)CBO}$	30	-	-	V	
Emitter-Base Breakdown Voltage at $-I_E=1mA$	$-V_{(BR)EBO}$	5	-	-	V	
Output Capacitance at $-V_{CB}=10V, f=1MHz$	Cob	-	48	-	pF	
Collector to Emitter Saturation Voltage at $-I_C=1.5A, -I_B=0.03A$	$-V_{CE(sat)}$	-	-	2	V	
Base-Emitter Voltage at $-V_{CE}=2V, -I_C=500mA$	$-V_{BE}$	-	-	1	V	
Transition Frequency at $-V_{CE}=2V, -I_C=500mA$	f_T	-	120	-	MHz	



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